Silicon P-Channel MOS FET

# HITACHI

November 1996

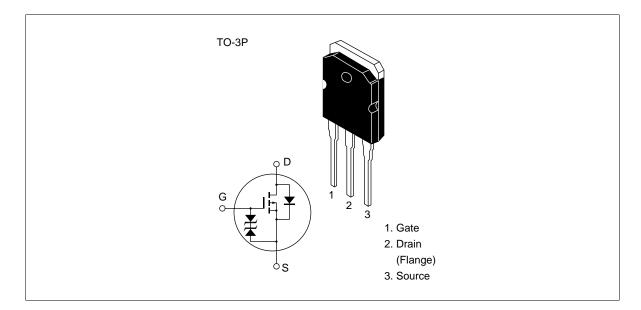
### Application

High speed power switching

#### Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
  - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

#### Outline





### **Absolute Maximum Ratings** (Ta = 25°C)

Symbol	Ratings	Unit
V <sub>DSS</sub>	-60	V
V <sub>GSS</sub>	±20	V
I <sub>D</sub>	-45	А
I *1 D(pulse)	-180	А
I <sub>DR</sub>	-45	А
Pch*2	150	W
Tch	150	٥C
Tstg	-55 to +150	٥C
	V <sub>DSS</sub> V <sub>GSS</sub> I <sub>D</sub> I <sub>D(pulse)</sub> * <sup>1</sup> I <sub>DR</sub> Pch* <sup>2</sup> Tch	$V_{DSS}$ -60 $V_{GSS}$ $\pm 20$ $I_D$ -45 $I_{D(pulse)}^{*1}$ -180 $I_{DR}$ -45           Pch* <sup>2</sup> 150           Tch         150

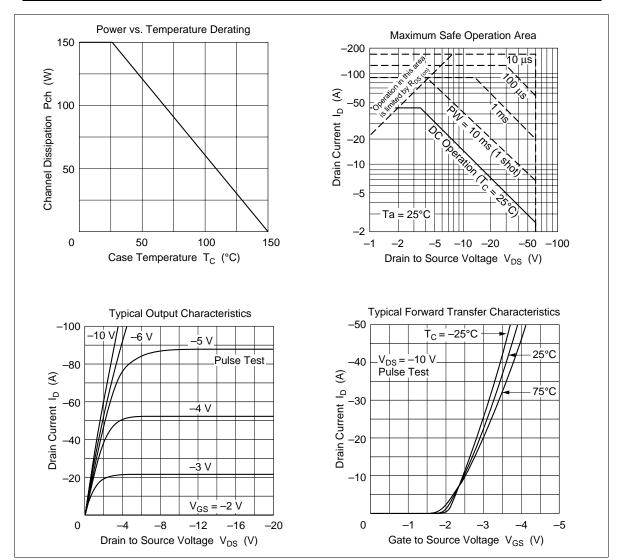
Notes 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

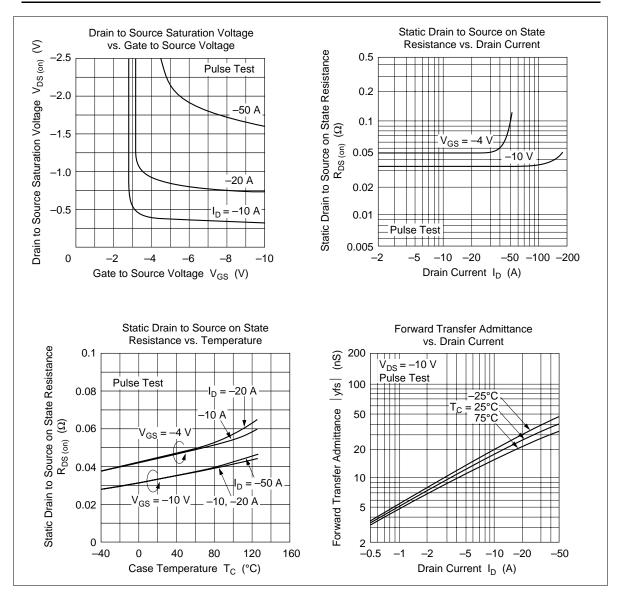
2. Value at T<sub>c</sub> =  $25^{\circ}$ C

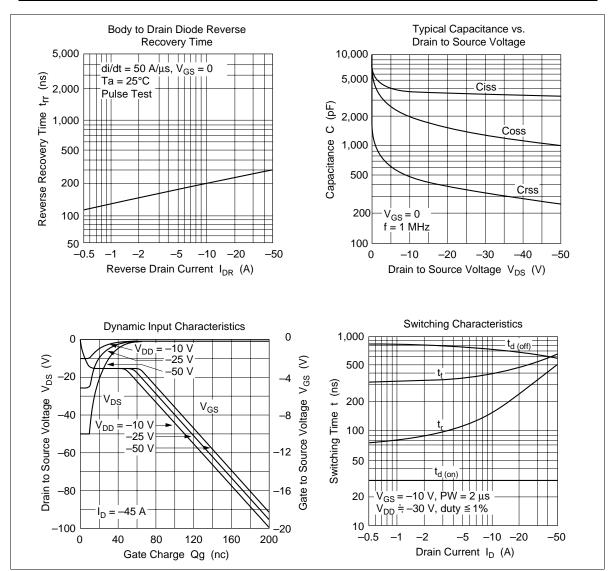
## **Electrical Characteristics** (Ta = 25°C)

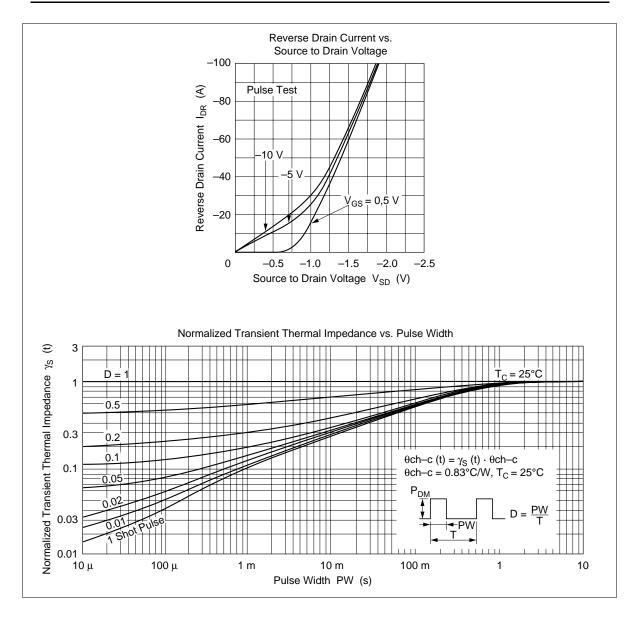
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	;
voltage       Gate to source leak current $I_{GSS}$ $\pm 10$ $\mu A$ $V_{GS} = \pm 16$ V, $V_{DS} = 200$ Zero gate voltage drain current $I_{DSS}$ -250 $\mu A$ $V_{DS} = -50$ V, $V_{GS} = 200$ Gate to source cutoff voltage $V_{GS(off)}$ -1.0        -220 $V$ $I_D = -1$ mA, $V_{DS} = 200$ Static drain to source on state $R_{DS(on)}$ -       0.033       0.042 $\Omega$ $I_D = -20$ A, $V_{GS} = 10$ resistance       -       0.045       0.06 $I_D = -20$ A, $V_{GS} = 10$ $I_D = -20$ A, $V_{GS} = 10$ Forward transfer admittance $ y_{ts} $ 16       25       -       S $I_D = -20$ A, $V_{GS} = 10$ Input capacitance       Ciss       -       3800       -       pF $V_{DS} = -10$ V, $V_{SS} = 10$ V_{DS} = -10 V, $V_{SS} = 10$ Output capacitance       Coss       -       2000       -       pF $I_D = -20$ A, $V_{GS} = 10$ V_{DS} = -10 V, $V_{SS} = 10$ V_{DS} = -20 A, $V_{GS} = 10$ V_{DS}	, = 0
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	<sub>s</sub> = 0
Gate to source cutoff voltage $V_{GS(off)}$ $-1.0$ $ -2.0$ V $I_D = -1 \text{ mA}, V_{DS} = 0$ Static drain to source on state $R_{DS(on)}$ $ 0.033$ $0.042$ $\Omega$ $I_D = -20 \text{ A}, V_{GS} = 0$ resistance $ 0.045$ $0.06$ $I_D = -20 \text{ A}, V_{GS} = 0$ Forward transfer admittance $ y_{fs} $ $16$ $25$ $ S$ $I_D = -20 \text{ A}, V_{GS} = 0$ Input capacitance       Ciss $ 3800$ $ pF$ $V_{DS} = -10 \text{ V}, V_{GS} = 0$ Output capacitance       Ciss $ 3800$ $ pF$ $V_{DS} = -10 \text{ V}, V_{GS} = 0$ Output capacitance       Ciss $ 3800$ $ pF$ $V_{DS} = -10 \text{ V}, V_{GS} = 0$ Turn-on delay time $t_{d(on)}$ $ 300$ $ pF$ $I_D = -20 \text{ A}, V_{GS} = 0$ Rise time $t_r$ $ 235$ $ ns$ $I_D = -20 \text{ A}, V_{GS} = 0$ Turn-off delay time $t_q$ $ 300$ $ ns$ $I_D = -20 \text{ A}, V_{GS} = 0$ $I_D = -20 \text{ A}, V_{GS} = 0$ <td>= 0</td>	= 0
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	= 0
resistance       -       0.045       0.06 $I_{\rm D} = -20$ Å, $V_{\rm GS} = 1$ Forward transfer admittance $ y_{\rm fs} $ 16       25       -       S $I_{\rm D} = -20$ Å, $V_{\rm GS} = 1$ Input capacitance       Ciss       -       3800       -       pF $V_{\rm DS} = -10$ V, $V_{\rm GS} = 10$ Output capacitance       Coss       -       2000       -       pF $f = 1$ MHz         Reverse transfer capacitance       Crss       -       490       -       pF         Turn-on delay time $t_{d(on)}$ -       30       -       ns $I_{\rm D} = -20$ Å, $V_{\rm GS} = 10$ Rise time $t_r$ -       2000       -       pF $f = 1$ MHz         Turn-on delay time $t_{d(on)}$ -       30       -       ns $I_{\rm D} = -20$ Å, $V_{\rm GS} = 10$ Rise time $t_r$ -       235       -       ns $R_{\rm L} = 1.5$ $\Omega$ Turn-off delay time $t_{d(off)}$ -       670       -       ns         Fall time $t_f$ -       450       -       ns	= –10 V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	-10 V*¹
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	: −4 V*1
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	-10 V*1
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	= 0,
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	-10 V,
Fall time         t <sub>f</sub> —         450         —         ns	
Body to drain diode forward $V_{DF}$ — -1.35 — V $I_F = -45 \text{ A}, V_{GS} = 0$	
voltage	0
Body to drain diode reverse $t_{rr}$ -300-ns $I_F = -45$ A, $V_{GS} = 0$ recovery time $di_F/dt = 50$ A/ $\mu s$	0,

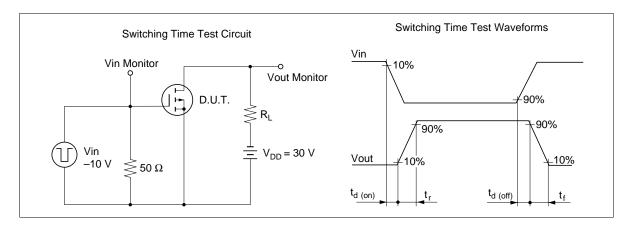
Note 1. Pulse test

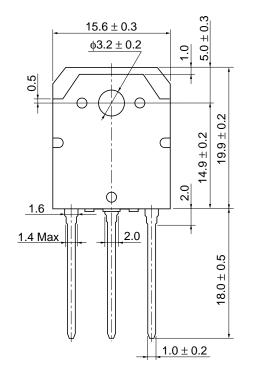


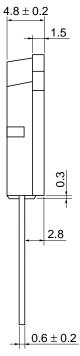






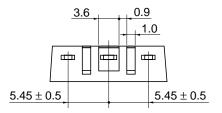








Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Weight (reference value)	5.0 g

#### Cautions

- 1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
- 2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
- 3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
- 4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
- 5. This product is not designed to be radiation resistant.
- 6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
- Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

# HITACHI

#### Hitachi, Ltd.

Semiconductor & Integrated Circuits. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109 URL NorthAmerica : http:semiconductor.hitachi.com/

NorthAmerica Europe Asia (Singapore) Asia (Taiwan) Asia (HongKong) Japan

http://www.hitachi-eu.com/hel/ecg http://www.has.hitachi.com.sg/grp3/sicd/index.htm http://www.hitachi.com.tw/E/Product/SICD\_Frame.htm http://www.hitachi.com.hk/eng/bo/grp3/index.htm http://www.hitachi.co.io/Sicd/indx.htm

#### For further information write to: Hitachi Semiconductor Hitachi Europe GmbH

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223

Electronic components Group Domacher Strage 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322 Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180 Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

Copyright ' Hitachi, Ltd., 1999. All rights reserved. Printed in Japan.